

NTD2955, NVD2955

MOSFET – Power, P-Channel, DPAK

-60 V, -12 A

This Power MOSFET is designed to withstand high energy in the avalanche and commutation modes. Designed for low-voltage, high-speed switching applications in power supplies, converters, and power motor controls. These devices are particularly well suited for bridge circuits where diode speed and commutating safe operating areas are critical and offer an additional safety margin against unexpected voltage transients.

Features

- Avalanche Energy Specified
- I_{DSS} and $V_{DS(on)}$ Specified at Elevated Temperature
- Designed for Low-Voltage, High-Speed Switching Applications and to Withstand High Energy in the Avalanche and Commutation Modes
- NVD and SVD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

| Rating | Symbol | Value | Unit |
|---|-----------------|------------|--------------------|
| Drain-to-Source Voltage | V_{DSS} | -60 | Vdc |
| Gate-to-Source Voltage | V_{GS} | ± 20 | Vdc |
| - Continuous | V_{GSM} | ± 25 | Vpk |
| - Non-repetitive ($t_p \leq 10$ ms) | | | |
| Drain Current | I_D | -12 | Adc |
| - Continuous @ $T_a = 25^\circ\text{C}$ | I_{DM} | -18 | Apk |
| - Single Pulse ($t_p \leq 10$ ms) | | | |
| Total Power Dissipation @ $T_a = 25^\circ\text{C}$ | P_D | 55 | W |
| Operating and Storage Temperature Range | T_J, T_{stg} | -55 to 175 | $^\circ\text{C}$ |
| Single Pulse Drain-to-Source Avalanche Energy – Starting $T_J = 25^\circ\text{C}$ ($V_{DD} = 25$ Vdc, $V_{GS} = 10$ Vdc, Peak $I_L = 12$ Apk, $L = 3.0$ mH, $R_G = 25$ Ω) | E_{AS} | 216 | mJ |
| Thermal Resistance | $R_{\theta JC}$ | 2.73 | $^\circ\text{C/W}$ |
| - Junction-to-Case | $R_{\theta JA}$ | 71.4 | |
| - Junction-to-Ambient (Note 1) | $R_{\theta JA}$ | 100 | |
| - Junction-to-Ambient (Note 2) | | | |
| Maximum Lead Temperature for Soldering Purposes, 1/8 in. from case for 10 seconds | T_L | 260 | $^\circ\text{C}$ |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

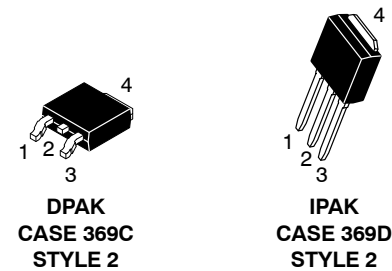
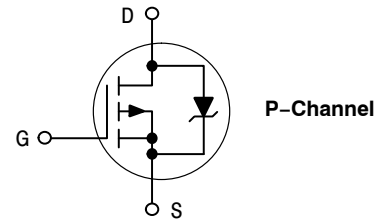
1. When surface mounted to an FR4 board using 1 in pad size (Cu area = 1.127 in²).
2. When surface mounted to an FR4 board using the minimum recommended pad size (Cu area = 0.412 in²).



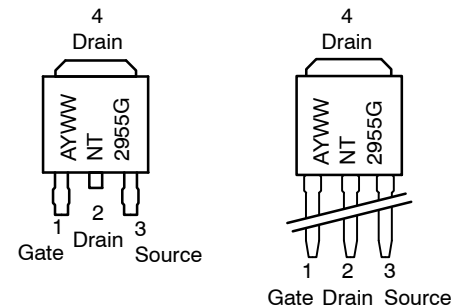
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| $V_{(BR)DSS}$ | $R_{DS(on)}$ TYP | I_D MAX |
|---------------|-----------------------------|-----------|
| -60 V | 155 m Ω @ -10 V, 6 A | -12 A |



MARKING DIAGRAMS & PIN ASSIGNMENTS



- A = Assembly Location*
- NT2955/NV2955 = Specific Device Code (DPAK)
- NT2955 = Specific Device Code (IPAK)
- Y = Year
- WW = Work Week
- G = Pb-Free Package

* The Assembly Location code (A) is front side optional. In cases where the Assembly Location is stamped in the package, the front side assembly code may be blank.

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

NTD2955, NVD2955

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|----------------|--------|-----|-----|-----|------|
|----------------|--------|-----|-----|-----|------|

OFF CHARACTERISTICS

| | | | | | |
|--|----------------------|----------|---------|-------------|--------------|
| Drain-to-Source Breakdown Voltage (Note 3) (V _{GS} = 0 Vdc, I _D = -0.25 mA) (Positive Temperature Coefficient) | V _{(BR)DSS} | -60 - | - 67 | - - | Vdc mV/°C |
| Zero Gate Voltage Drain Current (V _{GS} = 0 Vdc, V _{DS} = -60 Vdc, T _J = 25°C) (V _{GS} = 0 Vdc, V _{DS} = -60 Vdc, T _J = 150°C) | I _{DSS} | - - | - - | -10 -100 | μAdc |
| Gate-Body Leakage Current (V _{GS} = ± 20 Vdc, V _{DS} = 0 Vdc) | I _{GSS} | - | - | -100 | nAdc |

ON CHARACTERISTICS (Note 3)

| | | | | | |
|---|---------------------|-----------|-------------|--------------|--------------|
| Gate Threshold Voltage (V _{DS} = V _{GS} , I _D = -250 μAdc) (Negative Temperature Coefficient) | V _{GS(th)} | -2.0 - | -2.8 4.5 | -4.0 - | Vdc mV/°C |
| Static Drain-Source On-State Resistance (V _{GS} = -10 Vdc, I _D = -6.0 Adc) | R _{DS(on)} | - | 0.155 | 0.180 | Ω |
| Drain-to-Source On-Voltage (V _{GS} = -10 Vdc, I _D = -12 Adc) (V _{GS} = -10 Vdc, I _D = -6.0 Adc, T _J = 150°C) | V _{DS(on)} | | -1.86 - | -2.6 -2.0 | Vdc |
| Forward Transconductance (V _{DS} = 10 Vdc, I _D = 6.0 Adc) | g _{FS} | | 8.0 | - | Mhos |

DYNAMIC CHARACTERISTICS

| | | | | | | |
|------------------------------|--|------------------|---|-----|-----|----|
| Input Capacitance | (V _{DS} = -25 Vdc, V _{GS} = 0 Vdc, F = 1.0 MHz) | C _{iSS} | - | 500 | 750 | pF |
| Output Capacitance | | C _{oSS} | - | 150 | 250 | |
| Reverse Transfer Capacitance | | C _{rSS} | - | 50 | 100 | |

SWITCHING CHARACTERISTICS (Notes 3 and 4)

| | | | | | | |
|---------------------|---|---------------------|---|-----|----|----|
| Turn-On Delay Time | (V _{DD} = -30 Vdc, I _D = -12 A, V _{GS} = -10 V, R _G = 9.1 Ω) | t _{d(on)} | - | 10 | 20 | ns |
| Rise Time | | t _r | - | 45 | 85 | |
| Turn-Off Delay Time | | t _{d(off)} | - | 26 | 40 | |
| Fall Time | | t _f | - | 48 | 90 | |
| Gate Charge | (V _{DS} = -48 Vdc, V _{GS} = -10 Vdc, I _D = -12 A) | Q _T | - | 15 | 30 | nC |
| | | Q _{GS} | - | 4.0 | - | |
| | | Q _{GD} | - | 7.0 | - | |

DRAIN-SOURCE DIODE CHARACTERISTICS (Note 3)

| | | | | | |
|--|-----------------|--------|--------------|-----------|-----|
| Diode Forward On-Voltage (I _S = 12 Adc, V _{GS} = 0 V) (I _S = 12 Adc, V _{GS} = 0 V, T _J = 150°C) | V _{SD} | - - | -1.6 -1.3 | -2.5 - | Vdc |
| Reverse Recovery Time (I _S = 12 A, di _S /dt = 100 A/μs, V _{GS} = 0 V) | t _{rr} | - | 50 | | ns |
| | t _a | - | 40 | - | |
| | t _b | - | 10 | - | |
| Reverse Recovery Stored Charge | Q _{RR} | - | 0.10 | - | μC |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Indicates Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

4. Switching characteristics are independent of operating junction temperature.

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TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

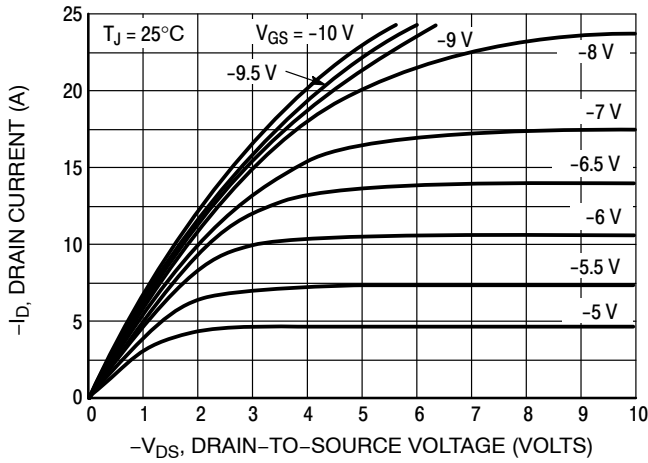


Figure 1. On-Region Characteristics

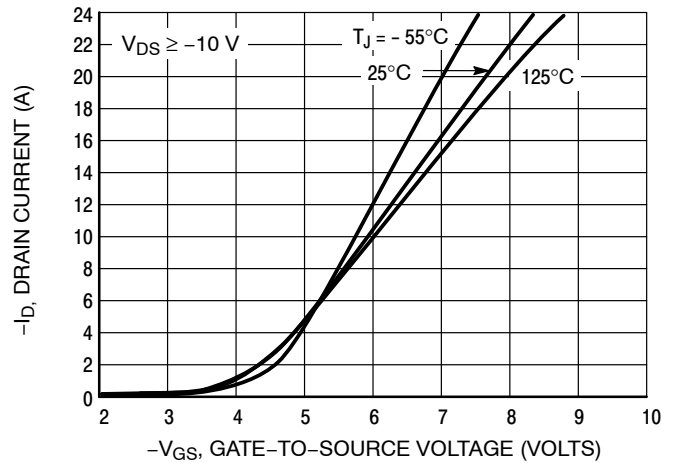


Figure 2. Transfer Characteristics

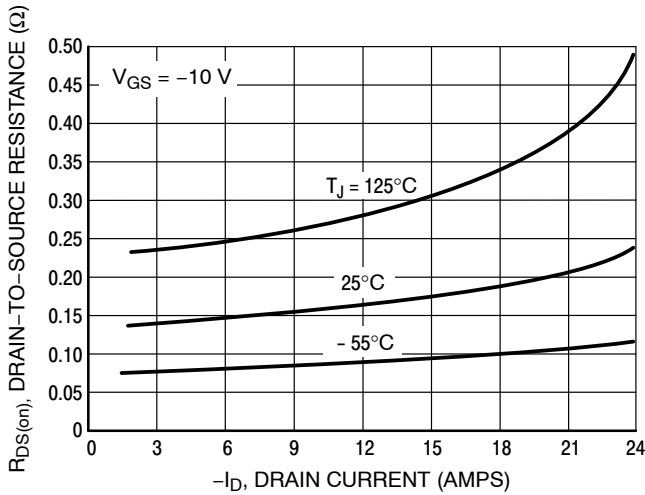


Figure 3. On-Resistance versus Drain Current and Temperature

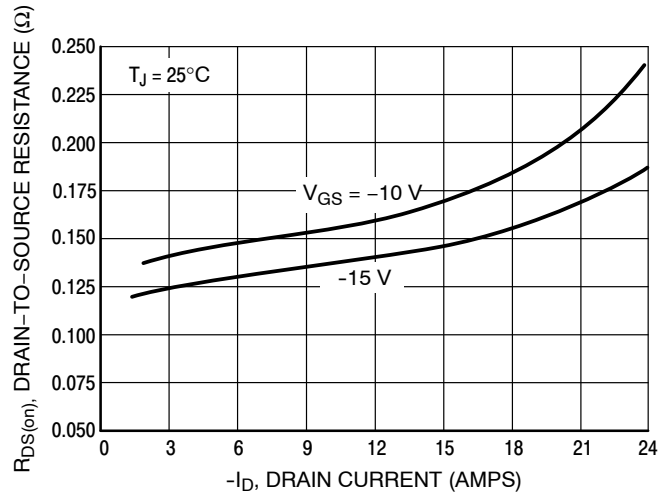


Figure 4. On-Resistance versus Drain Current and Gate Voltage

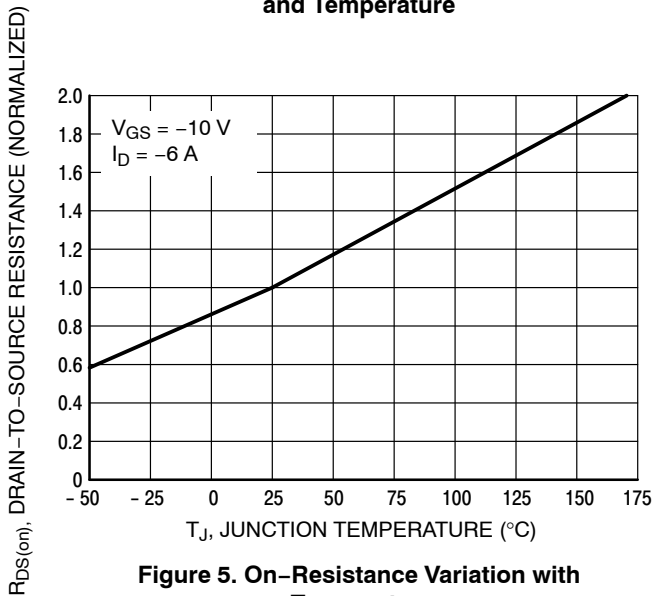


Figure 5. On-Resistance Variation with Temperature

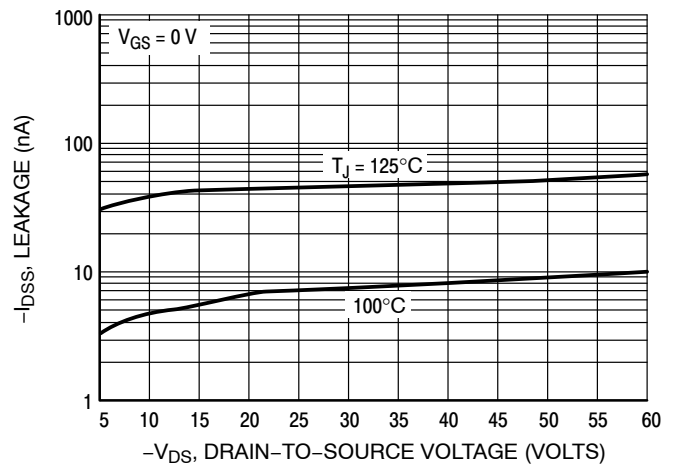


Figure 6. Drain-To-Source Leakage Current versus Voltage

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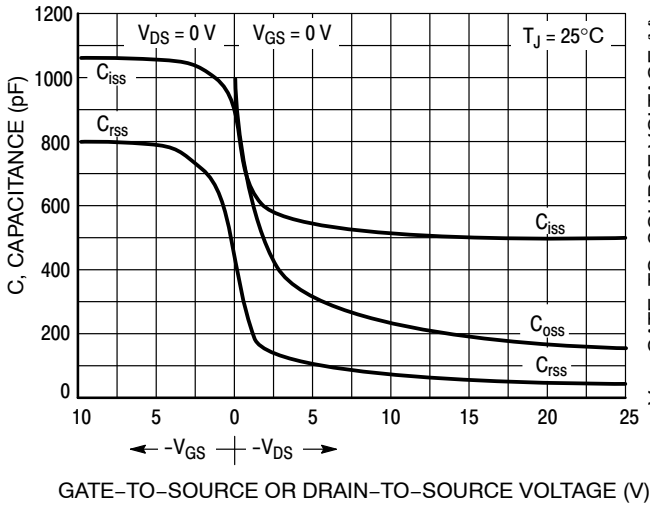


Figure 7. Capacitance Variation

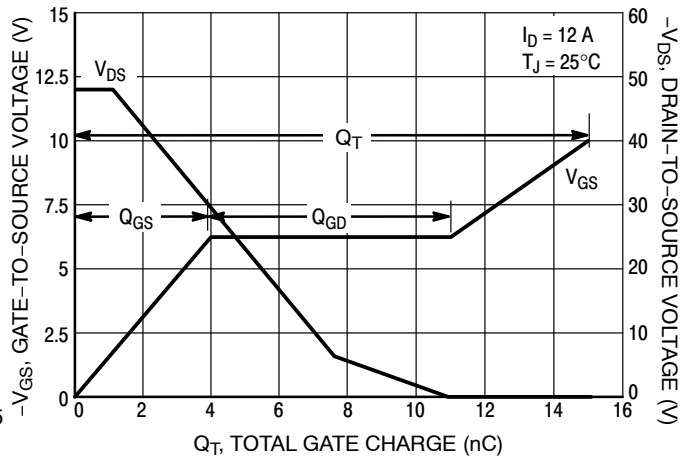


Figure 8. Gate-To-Source and Drain-To-Source Voltage versus Total Charge

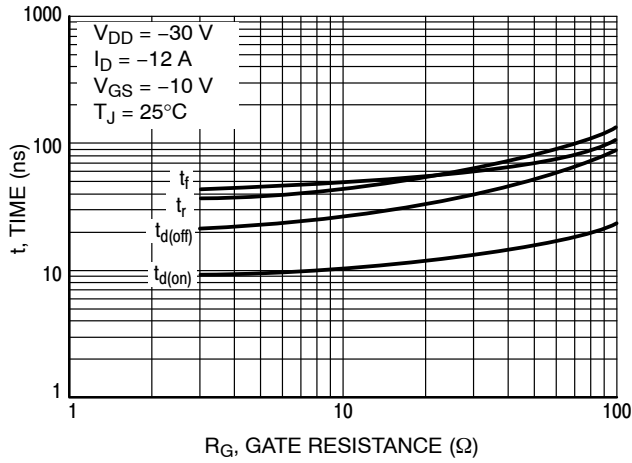


Figure 9. Resistive Switching Time Variation versus Gate Resistance

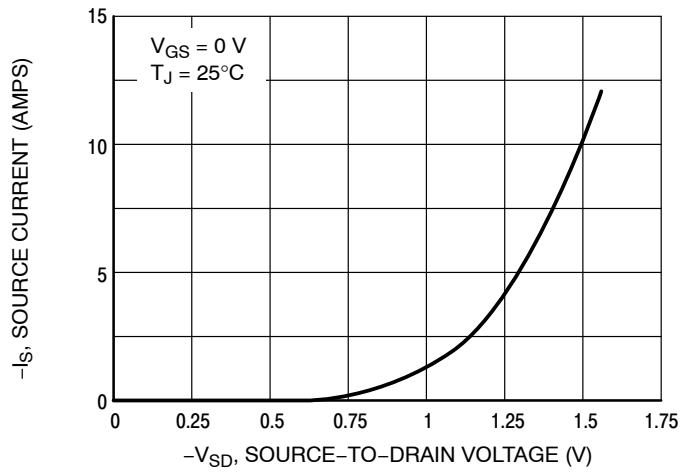


Figure 10. Diode Forward Voltage versus Current

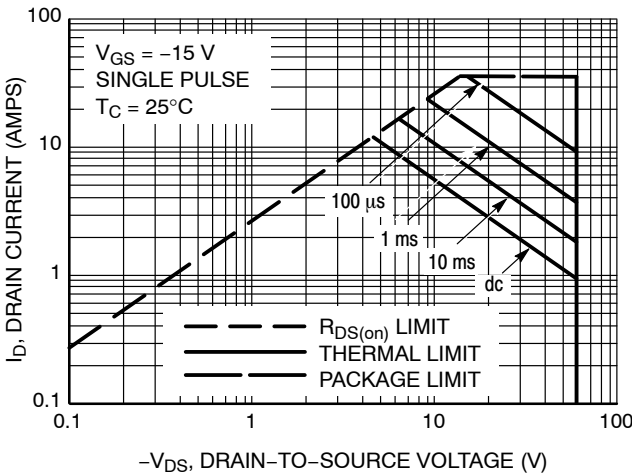


Figure 11. Maximum Rated Forward Biased Safe Operating Area

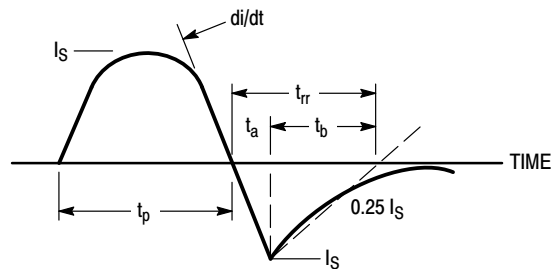


Figure 12. Diode Reverse Recovery Waveform

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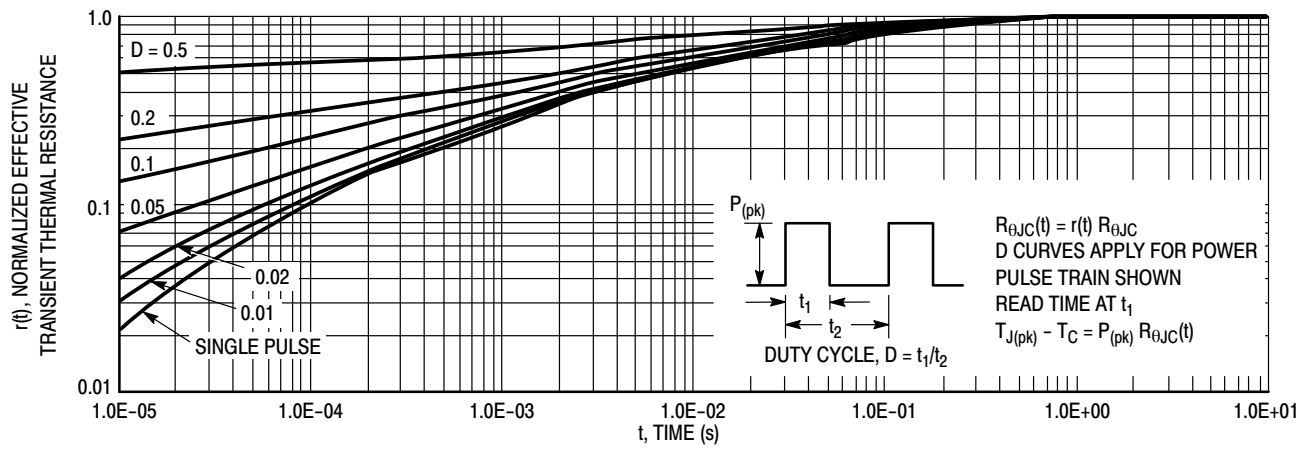


Figure 13. Thermal Response

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|-------------|-------------------|-----------------------|
| NTD2955G | DPAK (Pb-Free) | 75 Units / Rail |
| NTD2955-1G | IPAK (Pb-Free) | 75 Units / Rail |
| NTD2955T4G | DPAK (Pb-Free) | 2500 / Tape & Reel |
| NVD2955T4G* | DPAK (Pb-Free) | 2500 / Tape & Reel |
| SVD2955T4G* | DPAK (Pb-Free) | 2500 / Tape & Reel |

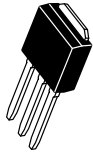
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NVD and SVD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

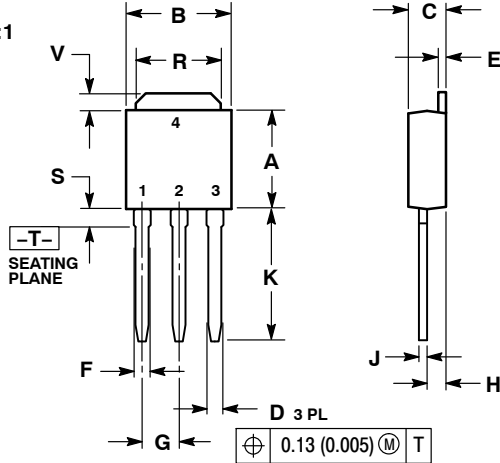
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IPAK CASE 369D-01 ISSUE C

DATE 15 DEC 2010

SCALE 1:1



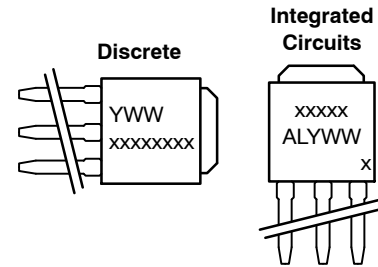
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

| DIM | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|------|
| | MIN | MAX | MIN | MAX |
| A | 0.235 | 0.245 | 5.97 | 6.35 |
| B | 0.250 | 0.265 | 6.35 | 6.73 |
| C | 0.086 | 0.094 | 2.19 | 2.38 |
| D | 0.027 | 0.035 | 0.69 | 0.88 |
| E | 0.018 | 0.023 | 0.46 | 0.58 |
| F | 0.037 | 0.045 | 0.94 | 1.14 |
| G | 0.090 | BSC | 2.29 | BSC |
| H | 0.034 | 0.040 | 0.87 | 1.01 |
| J | 0.018 | 0.023 | 0.46 | 0.58 |
| K | 0.350 | 0.380 | 8.89 | 9.65 |
| R | 0.180 | 0.215 | 4.45 | 5.45 |
| S | 0.025 | 0.040 | 0.63 | 1.01 |
| V | 0.035 | 0.050 | 0.89 | 1.27 |
| Z | 0.155 | --- | 3.93 | --- |

- | | | | |
|--|---|--|--|
| <p>STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR</p> | <p>STYLE 2: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN</p> | <p>STYLE 3: PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE</p> | <p>STYLE 4: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE</p> |
| <p>STYLE 5: PIN 1. GATE 2. ANODE 3. CATHODE 4. ANODE</p> | <p>STYLE 6: PIN 1. MT1 2. MT2 3. GATE 4. MT2</p> | <p>STYLE 7: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR</p> | |

MARKING DIAGRAMS



- xxxxxxxx = Device Code
- A = Assembly Location
- IL = Wafer Lot
- Y = Year
- WW = Work Week

| | | |
|-------------------------|------------------------------------|--|
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| DESCRIPTION: | IPAK (DPAK INSERTION MOUNT) | PAGE 1 OF 1 |

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